


a base substrate;
a first conducting film formed over the base substrate and including two conductor patterns adjacent to each other;
an etching stopper film covering each upper surface of the two conductor patterns;
a first insulation film formed over the etching stopper film and the base substrate;
a contact hole, located between the two conductor patterns, reaching the base substrate through the first insulation film, wherein an end of the contact hole is positioned above the respective conductor patterns; and
a sidewall insulation film formed on an inner wall of the first insulation film in the contact hole and on opposed side walls of the first conducting film and the etching stopper film in the contact hole.

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36. A semiconductor device according to claim 1, wherein
the end of the contact hole is defined by four sides including a first pair of sides which are opposed to each other and a second pair of sides which are opposed to each other,
the first pair of sides is defined by the conductor patterns, and
the second pair of sides is defined by the first insulation film.